



STTH20003TV

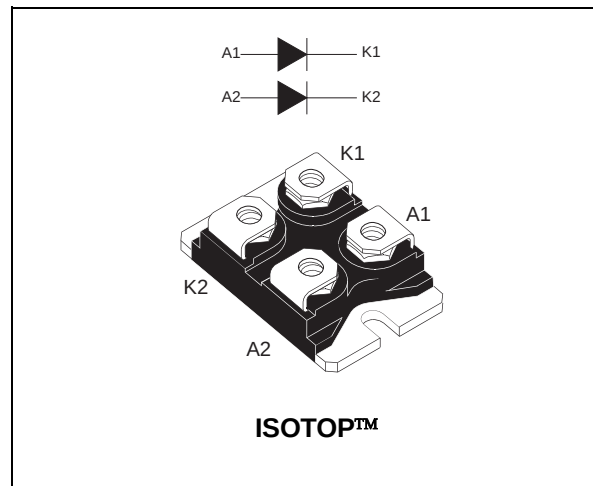
HIGH FREQUENCY SECONDARY RECTIFIER

MAJOR PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	2 x 100 A
V_{RRM}	300 V
T_j (max)	150 °C
V_F (max)	0.95 V
t_{rr} (max)	90 ns

FEATURES AND BENEFITS

- COMBINES HIGHEST RECOVERY AND REVERSE VOLTAGE PERFORMANCE
- ULTRAFAST, SOFT AND NOISE-FREE RECOVERY
- ISOLATED PACKAGE:
2500 V_{RMS} (UL APPROVAL PENDING DEVICE)
- LOW INDUCTANCE AND LOW CAPACITANCE
ALLOW SIMPLER LAYOUT



DESCRIPTION

Dual rectifiers suited for Switch Mode Power Supply and high frequency DC to DC converters.

Packaged in ISOTOP™, this device is intended for use in low voltage, high frequency inverters, free wheeling operation, welding equipment and telecom power supplies.

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage			300	V
I _{F(RMS)}	RMS forward current			180	A
I _{F(AV)}	Average forward current	T _c = 85°C δ = 0.5	Per diode Perdevice	100 200	A
I _{FSM}	Surge non repetitive forward current	tp = 10 ms sinusoidal		1000	A
I _{RSM}	Non Repetitive peak reverse current	tp = 100 μs square		13	A
T _{stg}	Storage temperature range			- 55 to + 150	°C
T _j	Maximum operating junction temperature			150	°C

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THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode Total	0.55 0.35	$^{\circ}\text{C/W}$
$R_{th(c)}$		Coupling	0.1	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j (\text{diode 1}) = P (\text{diode 1}) \times R_{th(j-c)} (\text{per diode}) + P (\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$V_R = 300\text{ V}$	$T_j = 25^{\circ}\text{C}$			200	μA
			$T_j = 125^{\circ}\text{C}$		0.2	2	mA
V_F^{**}	Forward voltage drop	$I_F = 100\text{ A}$	$T_j = 25^{\circ}\text{C}$			1.20	V
			$T_j = 125^{\circ}\text{C}$		0.8	0.95	

Pulse test : * $t_p = 5\text{ ms}$, $\delta < 2\%$

** $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation:

$$P = 0.75 \times I_{F(AV)} + 0.0020 \times I_F^2 (RMS)$$

RECOVERY CHARACTERISTICS

Symbol	Tests Conditions			Min.	Typ.	Max.	Unit
trr	I _F = 0.5 A	I _{rr} = 0.25 A	I _R = 1A	T _j = 25°C		55	ns
	I _F = 1 A	di _F /dt = - 50 A/μs	V _R = 30 V			90	
tfr	I _F = 100 A	di _F /dt = 200 A/μs		T _j = 25°C		1400	ns
V _{FP}	V _{FR} = 1.1 x V _F max.					5	V
S _{factor}	V _{CC} = 200 V	I _F = 100 A		T _j = 125°C		0.3	-
I _{RM}	di _F /dt = 200 A/μs					18	A

Fig. 1: Conduction losses versus average current (per diode).

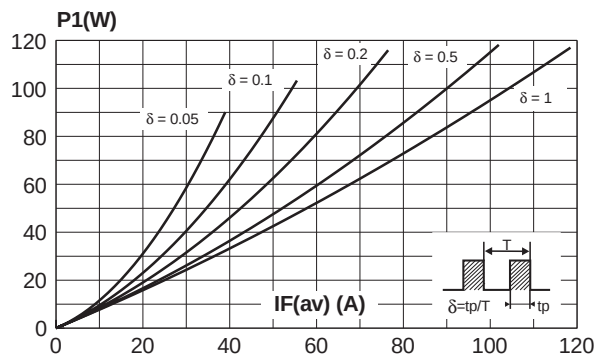


Fig. 2: Forward voltage drop versus forward current (Maximum values, per diode).

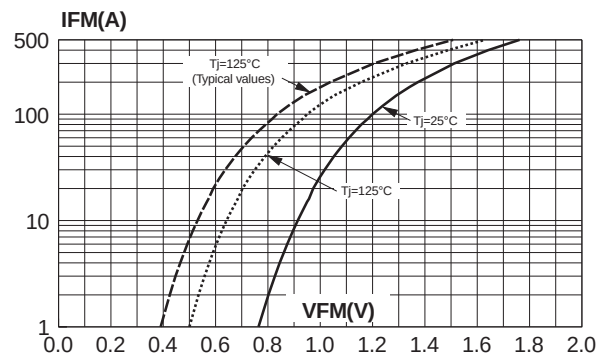


Fig. 3: Relative variation of thermal impedance junction to case versus pulse duration.

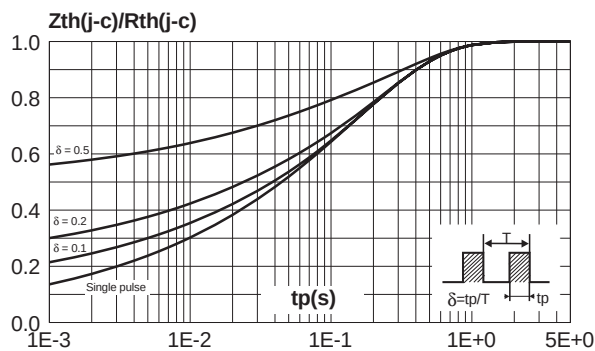


Fig. 4: Peak reverse recovery current versus dIF/dt (90% confidence, per diode).

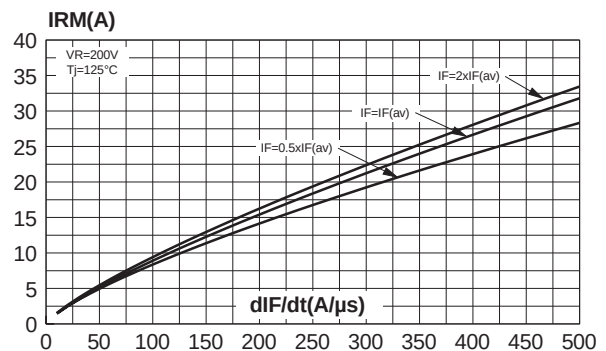


Fig. 5: Reverse recovery time versus dIF/dt (90% confidence, per diode).

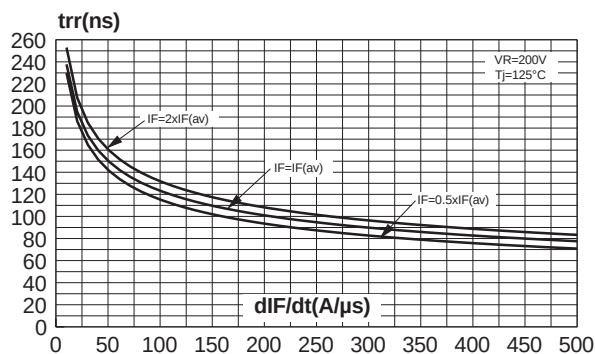


Fig. 6: Softness factor (tb/ta) versus dIF/dt (typical values, per diode).

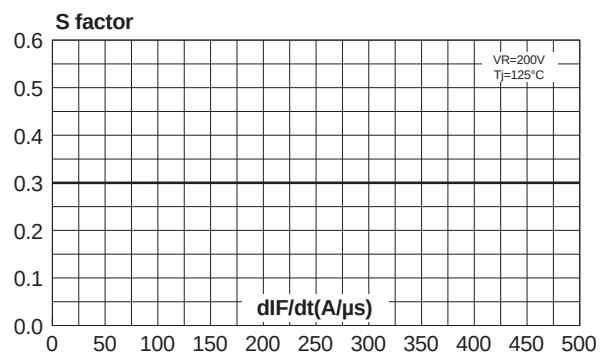


Fig. 7: Relative variation of dynamic parameters versus junction temperature (Reference: $T_J=125^{\circ}\text{C}$).

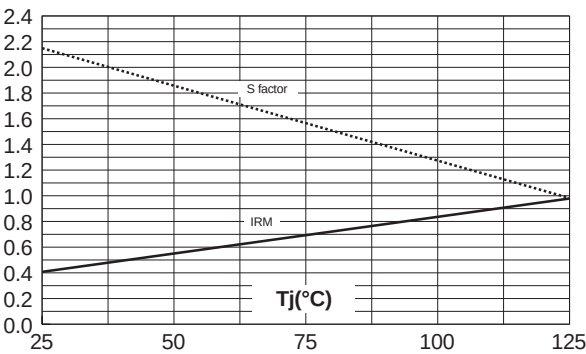


Fig. 8: Transient peak forward voltage versus dI_F/dt (90% confidence, per diode).

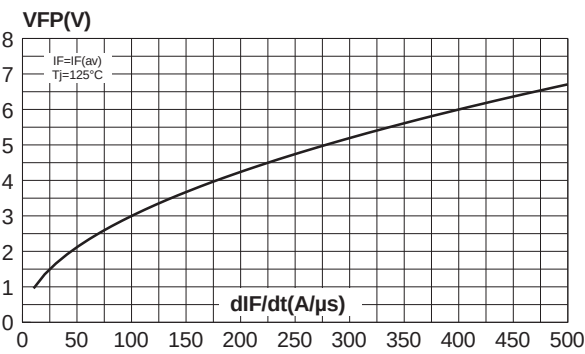
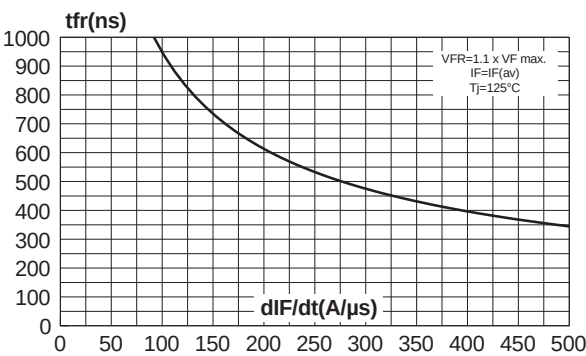
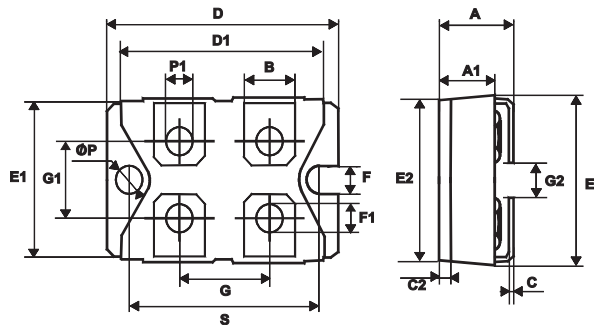


Fig.9: Forward recovery time versus dI_F/dt (90% confidence, per diode).



PACKAGE MECHANICAL DATA
ISOTOP


REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.465	0.480
A1	8.90	9.10	0.350	0.358
B	7.8	8.20	0.307	0.323
C	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
E	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80 typ.		0.976 typ.	
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5.00	0.181	0.197
P	4.00	4.30	0.157	0.69
P1	4.00	4.40	0.157	0.173
S	30.10	30.30	1.185	1.193

- Cooling method: by conduction (C)
- Recommended torque value : 1.3 N.m.
- Maximum torque value: 1.5 N.m.

Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH20003TV	STTH20003TV	ISOTOP	27g. without screws	10 with screws	Tube

- Epoxy meets UL 94,V0

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